

## DiplETE – CS (OLD SCHEME)

Code: DC02  
Time: 3 Hours

Subject: FUNDAMENTALS OF ELECTRONICS  
Max. Marks: 100

**JUNE 2011**

NOTE: There are 9 Questions in all.

- Question 1 is compulsory and carries 20 marks. Answer to Q.1 must be written in the space provided for it in the answer book supplied and nowhere else.
- The answer sheet for the Q.1 will be collected by the invigilator after 45 Minutes of the commencement of the examination.
- Out of the remaining EIGHT Questions answer any FIVE Questions. Each question carries 16 marks.
- Any required data not explicitly given, may be suitably assumed and stated.

**Q.1 Choose the correct or the best alternative in the following: (2×10)**

- a. The input impedance of an ideal op-amp is \_\_\_\_\_
- (A) Zero. (B) Infinity.  
(C)  $100\Omega$ . (D) Less than one.
- b. A resistor has a colour band sequence Green, Violet, Black and gold. Its value is \_\_\_\_\_
- (A)  $5.7\Omega \pm 5\%$ . (B)  $57\Omega \pm 5\%$ .  
(C)  $570\Omega \pm 5\%$ . (D)  $5.7\text{K}\Omega \pm 5\%$ .
- c. Oscillators uses \_\_\_\_\_ feedback.
- (A) Positive. (B) Negative.  
(C) Both (A) and (B). (D) None of above.
- d. An electron in the conduction band \_\_\_\_\_
- (A) has no energy.  
(B) has a less energy than an electron in the valance band.  
(C) has equal energy than an electron in the valance band.  
(D) has a higher energy than an electron in the valance band.
- e. When the P-N junction is forward biased, width of depletion layer is \_\_\_\_\_
- (A) reduced. (B) increased.  
(C) same as unbiased. (D) none of above.
- f. The Schottky barrier diode has \_\_\_\_\_
- (A) one p-n junction. (B) two p-n junction.  
(C) no p-n junction. (D) none of them is true.

- g. In a junction transistor, which region is made narrower than the other two regions \_\_\_\_\_
- (A) collector region. (B) base region.  
(C) emitter region. (D) none of above.
- h. Which of the following is a universal gate \_\_\_\_\_
- (A) AND (B) NAND  
(C) OR (D) NOT
- i. The main advantage of CMOS is \_\_\_\_\_
- (A) high speed. (B) low noise margins.  
(C) low power consumption. (D) none of above.
- j. The plastic DIP IC package is most widely used, because \_\_\_\_\_
- (A) it has higher mechanical strength.  
(B) it is only packing method available.  
(C) other type of packing method is not reliable.  
(D) it is much cheaper than other type of packages.

**Answer any FIVE Questions out of EIGHT Questions.**  
**Each question carries 16 marks.**

- Q.2** a. Explain the working of electrolytic capacitor with the help of its constructional details. (8)
- b. Explain how will you convert a current source into a voltage source. Also state and explain Thevenin's theorem. (4+4)
- Q.3** a. What are intrinsic and extrinsic semiconductors? Explain effect of temperature on conductivity of semiconductor. (4+4)
- b. What is p-n junction diode? How potential barrier is formed in a p-n junction diode? What is its significance? (3+3+2)
- Q.4** a. Draw the V-I characteristics of Tunnel diode and explain its working principle. (8)
- b. Explain the term doping and its need. Draw energy band diagram for N-type and P-type semiconductors and indicate the position of the Fermi, the donor and the acceptor levels. (4+4)
- Q.5** a. Explain the transistor action with the help of suitable diagram and also explain need for transistor biasing. (4+4)

- b. Compare the CB, CE and CC configurations of a transistor. Draw input and output characteristics of a transistor in CB configuration. (4+4)
- Q.6** a. Explain the differences between positive and negative feedback amplifier. What are advantages & disadvantages of negative feedback amplifier? (4+4)
- b. With the help of a diagram, explain the working of FET as a switch. Also list out the applications of FET. (4+4)
- Q.7** a. Prove the following using Boolean algebra  
 (i)  $A(A+B) + A(B+C) + A(A+C) = A$   
 (ii)  $(A+B)(\bar{A}+C)(B+C) = AC + B\bar{A}$  (4+4)
- b. Minimize the following logic functions using K- Map  

$$f(A, B, C, D) = \sum m(1,3,5,8,9,11,15) + d(2,13)$$
 (8)
- Q.8** a. Draw schematic diagram of TTL NAND gate and explain its working. (8)
- b. Draw symbol of EX-OR gate and explain its working using truth table. Also realize EX-OR gate using four NAND gates only. (4+4)
- Q.9** a. What is IC? Explain how a capacitor can be constructed in a monolithic IC. (8)
- b. Draw the schematic diagram of Integrator and Voltage Follower using op-amp and explain its working. (4+4)